

IN THE SPECIFICATION:

Please amend paragraph [0052] in the specification as follows:

[0052] Fig. 3 is a perspective view showing the configuration of the semiconductor laser array 3. The semiconductor laser array 3 has plural active layers 3a arranged in parallel along the y-axis direction. Each active layer 3a emits a laser beam along an optical axis A, where the optical axis A passes through the center of each active layer 3a in parallel with the x-axis. Fig. 4A is a view showing the front end surface (beam emitting surface) of the semiconductor laser array 3, while Fig. 4B is a view showing the front end surface of each active layer 3a. The semiconductor laser array 3 has a structure in which active layers 3a are arranged in line in the y-axis direction with a spacing of 500 μ m within a width of 1cm. The cross-section of the active layers 3a has a width of 150 μ m and a thickness of 1 μ m. Also, the front end surface of the semiconductor laser array 3 is coated with a ~~reflection film~~ reflection suppressing film having a reflectance of several % or less.

Please amend paragraph [0066] in the specification as follows:

[0066] The arrangement above forms an external resonator between the reflecting portions 9a and the active layers 3a and causes stimulated emission in the active layers 3a due to resonance of part of beams in the external resonator. This causes the spatial transverse mode of laser beams to be emitted in a stimulated manner to be brought close to a single mode. Meanwhile, beam that enters each transmitting portion 9b of the optical element 9 from the collimator lens 5 transmits via the transmitting portion 9b to be emitted outside the semiconductor laser device 100 [[1]]. This is the final output from the semiconductor laser device 100.

Please amend paragraph [0096] in the specification as follows:

[0096] The arrangement above forms an external resonator between the reflecting portions 9a of the optical element 9 and the wavelength selecting element 10, the active layers 3a being positioned within the resonator, and causes stimulated emission in the active layers 3a due to resonance of part of beams in the external resonator. This causes the spatial transverse mode of laser beams to be emitted in a stimulated manner to be brought close to a single mode. Meanwhile, the beam that transmits through the wavelength selecting element 10 [[8]] is emitted outside the semiconductor laser device 130 [[1]]. This is the final output from the semiconductor laser device 130 [[1]].

Please amend paragraph [0102] in the specification as follows:

[0102] The semiconductor laser device 140 according to the fifth ~~second~~ embodiment differs from the semiconductor laser device 130 according to the fourth embodiment (Figs. 14A and 14B) in that the wavelength selecting element 10 is provided between the collimator lens 5 and the optical element 9. Except for the difference, the configuration of the semiconductor laser device 140 is the same as that of the semiconductor laser devices 100 and 130 according to the first and fourth embodiments, and the descriptions will be omitted.

Please amend paragraph [0126] in the specification as follows:

[0126] The semiconductor laser device 180 according to the ninth embodiment, however, differs from the semiconductor laser device 130 according to the fourth embodiment (Figs. 14A and 14B) in that the optical element 9 is inclined by about 45° with respect to a plane perpendicular to the optical axis of beams emitted from the semiconductor laser array 3, and that the

wavelength selecting element 10 is arranged in a position where beam reflected at the optical element 9 reaches. Except for the difference, the configuration of the semiconductor laser device 180 ~~[[160]]~~ is the same as that of the semiconductor laser devices 130 to 170 according to the fourth to eighth embodiments, and the descriptions will be omitted.

Please amend paragraph [0135] in the specification as follows:

[0135] Each semiconductor laser array 3 has the same configuration as that of the semiconductor laser array 3 in the first embodiment (Figs. 3, 4A and 4B). Each collimator lens 5 also has the same configuration as that in the first embodiment (Fig. 6). Each optical element 9 has the same configuration as that in the third embodiment (Fig. 13) (~~Fig. 7~~). Further, the wavelength selecting element 10 has approximately the same configuration as that in the fourth embodiment (Fig. 15). The semiconductor laser array 3, collimator lens 5, wavelength selecting element 10, and optical element 9 are arranged in the same manner as in the ninth embodiment.

Please amend paragraph [0139] in the specification as follows:

[0139] The semiconductor laser device 200 according to the eleventh embodiment, however, differs from the semiconductor laser device 180 according to the ninth embodiment (Figs. 20A and 20B) in that the wavelength selecting element 10 is arranged in a position where beam that transmits through each transmitting portion 9b of the optical element 9, and that the wavelength selecting element 10 is arranged in a position where beam reflected at the optical element 9 reaches. Except for the difference, the configuration of the semiconductor laser device 200 ~~[[160]]~~ is the same as that of the semiconductor laser devices 130 to 170 according to the fourth to eighth embodiments, and the descriptions will be omitted.